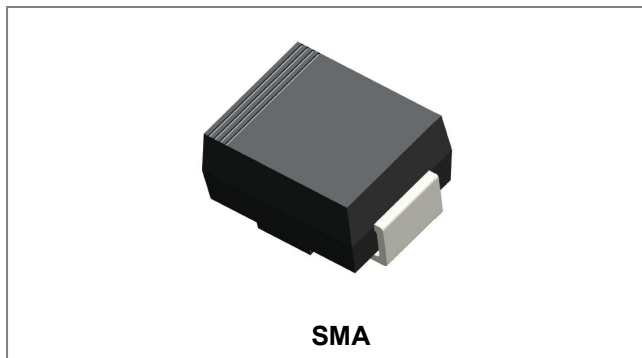


ES2A-ES2J SURFACE MOUNT SUPER FAST RECTIFIER



Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Overload Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: Low Profile Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.06 grams(approx)

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Characteristic	Symbol	ES2A	ES2B	ES2C	ES2D	ES2E	ES2G	ES2J	Units
Peak Repetitive Reverse Voltage	V _{RRM}	50	100	150	200	300	400	600	V
Working Peak Reverse Voltage	V _{RWM}								
DC Blocking Voltage	V _R								
RMS Reverse Voltage	V _{R(RMS)}	34	70	105	140	210	280	420	
Average Rectified Output Current @T _L = 110°C	I _O	2.0							A
Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	50							A
Forward Voltage @I _F = 2.0A, T _J =25°C	V _F	0.95				1.25	1.7		V
Maximum DC reverse current T _A = 25°C at rated DC blocking voltage T _A = 100°C	I _R	5.0 500							μA
Typical junction capacitance (Note 1)	C _J	25							pF
Maximum Reverse Recovery Time (Note 2)	T _{rr}	35							ns
Typical thermal resistance (Note 3)	R _{θJL}	20							K/W
Operating junction and storage temperature range	T _J , T _{STG}	-55 to +150							°C

Note: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0 V_{DC}
2. Measured with I_F=0.5A, I_R=1.0A, I_{rr}=0.25A
3. Mounted on P.C. Board with 8.0mm² lead area

Ratings and Characteristics Curves

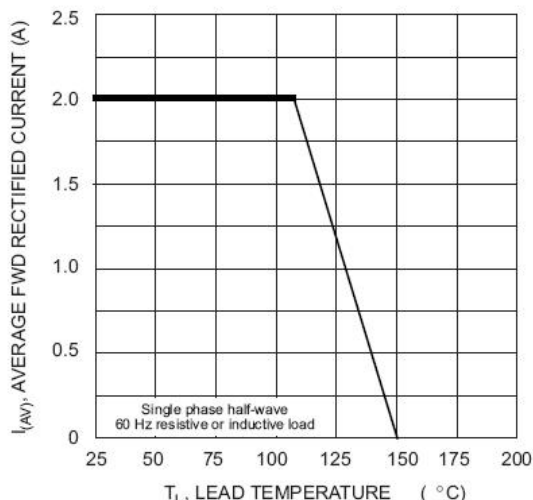


Fig. 1 Forward Current Derating Curve

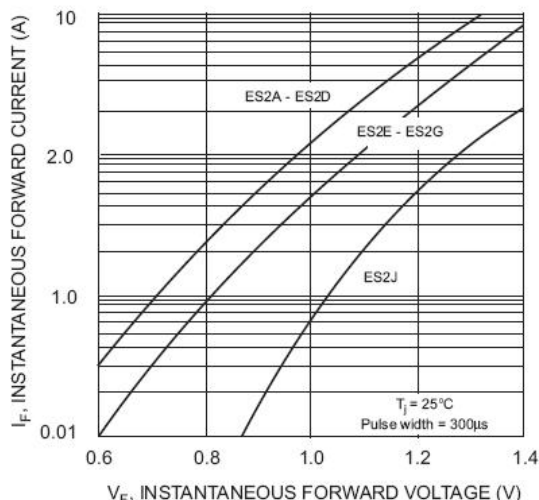


Fig. 2 Typical Forward Characteristics

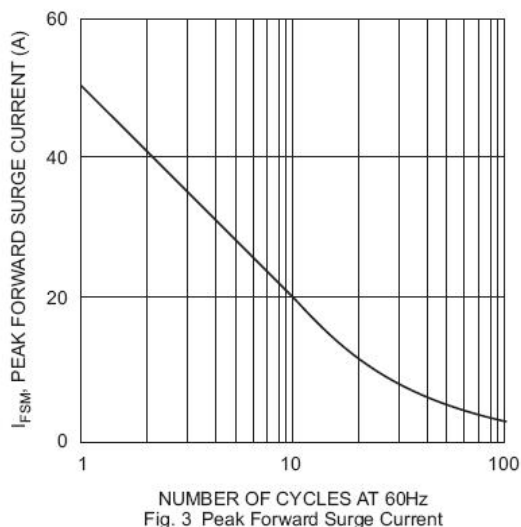


Fig. 3 Peak Forward Surge Current

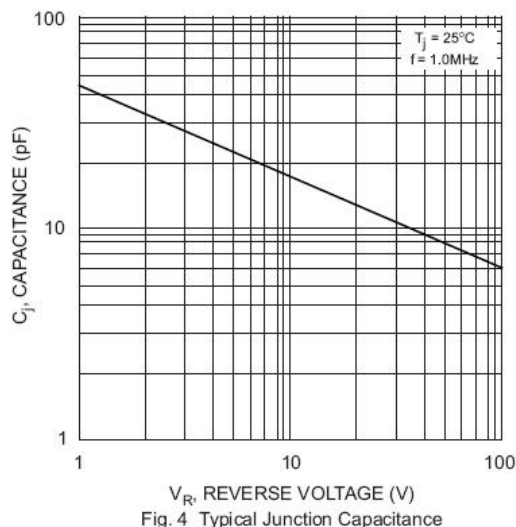
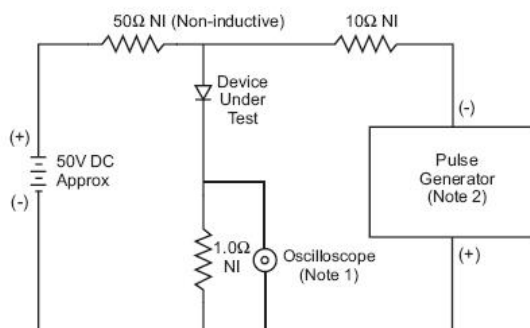
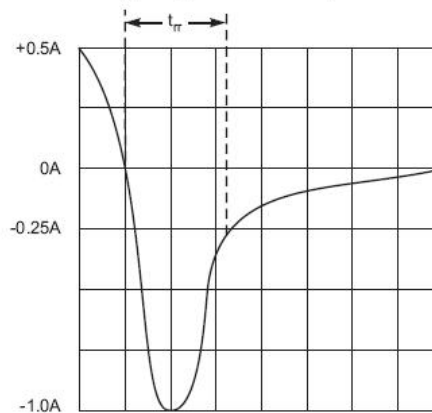


Fig. 4 Typical Junction Capacitance



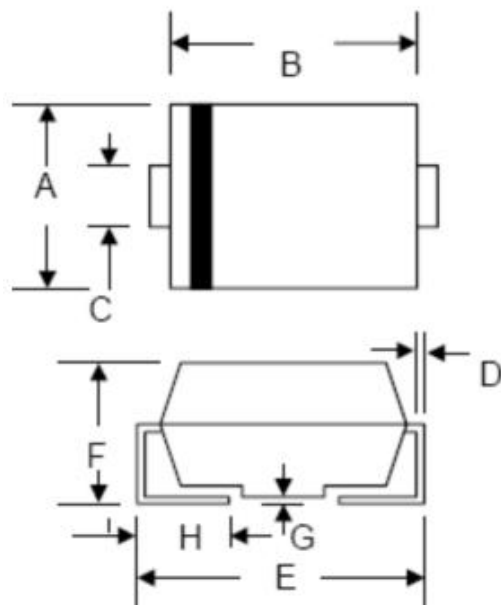
- Notes:
1. Rise Time = 7.0ns max. Input Impedance = 1.0M Ω , 22pF.
2. Rise Time = 10ns max. Input Impedance = 50 Ω .



Set time base for 5/10ns/cm

Fig. 5 Reverse Recovery Time Characteristic and Test Circuit

Mechanical Dimensions SMA



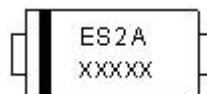
SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.18	2.90	0.086	0.114
B	3.99	4.60	0.157	0.181
C	1.29	1.70	0.508	0.067
D	0.152	0.305	0.006	0.012
E	4.70	5.31	0.185	0.209
F	1.70	2.50	0.067	0.098
G	0.051	0.203	0.002	0.008
H	0.76	1.55	0.030	0.610

Ordering Information

Device	Package	Shipping
ES2A-ES2M	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

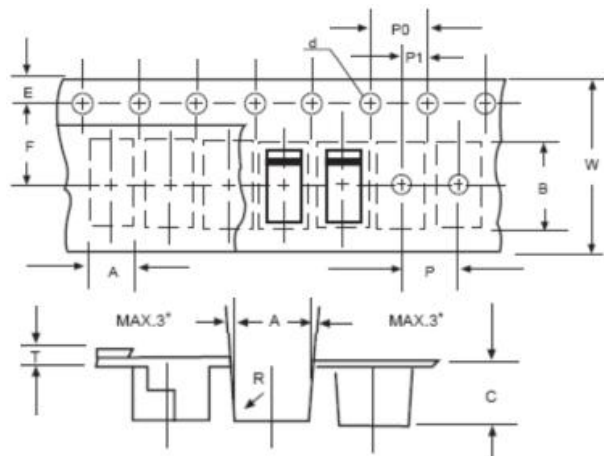


Where XXXXX is YYWWL

ES = Device Type
2 = Forward Current (2A)
A = Reverse Voltage (50V)
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification SMA



SYMBOL	Millimeters	
	Min.	Max.
A	2.97	3.17
B	5.70	5.90
C	2.32	2.52
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	3.90	4.10
P0	3.90	4.10
P1	1.90	2.10
T	0.25	0.35
W	11.80	12.20

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